

Attorney Docket No.: MIO 0104 VA/40509.259
Application Number: 10/650,563

Please replace the ABSTRACT with the following amended ABSTRACT.

ABSTRACT OF THE DISCLOSURE

A method of manufacturing a memory device addressing reliability and refresh characteristics through the use of a multilayered doped conductor, and a method-making is are disclosed. The multilayered doped conductor creates a high dopant concentration in the active area close to the channel region. The rich dopant layer created by the multilayered doped conductor is less susceptible to depletion from trapped charges in the oxide. This improves device reliability at burn-in and lowers junction leakage, thereby providing a longer period between refresh cycles.